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Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

FEATURES AND BENEFITS

- Accurate power monitoring of AC/DC applications
- Reinforced isolation up to 517 V_{RMS} in a single package eliminates the need for dual isolated supplies (certification pending)
- Active, reactive, and apparent power measurements, and power factor
- RMS and instantaneous voltage and current measurements
- $0.85 \text{ m}\Omega$ primary conductor resistance for low power loss and high inrush current withstand capability
- Dedicated voltage zero crossing pin
- Overcurrent fault output pin
- Hall-effect-based current measurement with commonmode stray field rejection
- User-programmable V_{RMS} under/overvoltage pin
- 1 kHz bandwidth
- Current-sensing range from 0 to 90 A
- I²C or SPI communication
- User-programmable through EEPROM registers
- 16-bit voltage and current ADCs

PACKAGE

16-pin SOICW (suffix MA)

Not to scale

DESCRIPTION

The ACS71020 power monitoring IC greatly simplifies the addition of power monitoring to any AC/DC powered device. By making use of Allegro's Hall-effect-based, galvanically isolated integrated current sensor technology, reinforced isolation can be achieved. The sensor can be powered from the same supply as the MCU, eliminating the need for multiple power supplies and digital isolation ICs.

The isolated current measurement is done by detecting the magnetic field from the integrated conductor, eliminating the need for external sense resistors, current transformers, or Rogowski coils. Two Hall plates are used for this measurement to differentially sense the field, thus eliminating errors due to stray magnetic fields. Multiple parameters like bandwidth, averaging time, and fault levels are user-programmable.

The sensor features all key power measurements, which can be read out through I²C or SPI, as well as dedicated pins for voltage zero crossing (suitable for light-dimming applications) and fast overcurrent fault (for short-circuit detection). As the sensor is isolated, these pins can be easily accessed by the MCU without additional isolation to each signal. These two pins can also be configured to flag a V_{RMS} under/overvoltage.

The ACS71020 is provided in a small, low-profile, surface-mount SOIC16 wide-body package. The ACS71020 is lead (Pb) free, and is fully calibrated prior to shipment from the factory. Further customer calibration in application can improve accuracy.

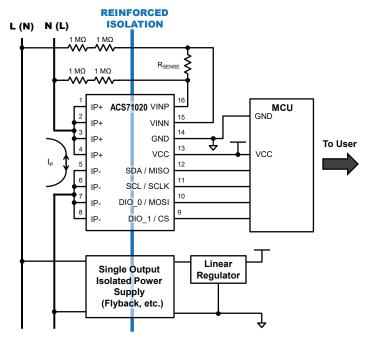


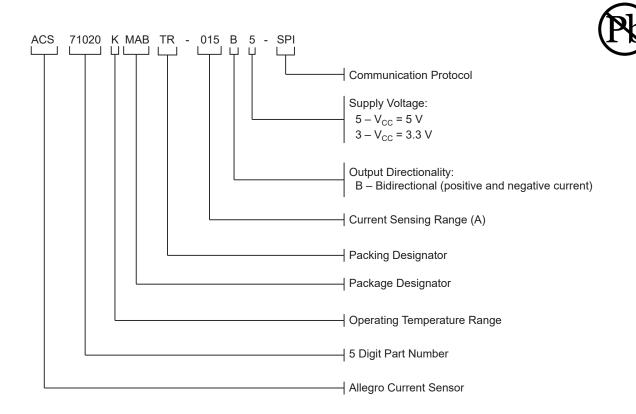
Figure 1: Typical Application

Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

SELECTION GUIDE

Part Number	V _{CC(NOM)} (V)	I _{PR} (A)	Communication Protocol	T _A (°C)	Packing ^[1]
ACS71020KMABTR-015B5-SPI	5	±15	SPI		
ACS71020KMABTR-030B3-SPI	3.3	±30	581	40 to 405	Tape and reel,
ACS71020KMABTR-030B3-I2C	3.3	±30			1000 pieces per reel, 3000 pieces per box
ACS71020KMABTR-090B3-I2C	3.3	±90	140		

^[1] Contact Allegro for additional packing options.





Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Notes	Rating	Units
Supply Voltage	V _{CC}		6.5	V
Reverse Supply Voltage	V _{RCC}		-0.5	V
Input Voltage	V _{INP} , V _{INN}		V _{CC} + 0.5	V
Reverse Input Voltage	V _{RNP} , V _{RNN}		-0.5	V
Digital I/O Voltage	V _{DIO}		6	V
Reverse Digital I/O Voltage	V _{RDIO}	SPI, I ² C, and general purpose I/O	-0.5	V
Operating Ambient Temperature	T _A	Range K	-40 to 125	°C
Junction Temperature	T _J (max)		165	°C
Storage Temperature	T _{stg}		–65 to 170	°C

ISOLATION CHARACTERISTICS

Characteristic	Symbol	Notes	Rating	Unit		
Dielectric Strength Test Voltage	V _{ISO}	Agency type-tested for 60 seconds per UL 60950-1 (edition 2). Production tested at 3000 V_{RMS} for 1 second, in accordance with UL 60950-1 (edition 2). (certification pending)	4800	V _{RMS}		
Working Voltage for Basic Isolation		Maximum approved working voltage for basic (single) isolation		Maximum approved working voltage for basic (single) isolation	1480	V _{PK}
Working voltage for basic isolation	V _{WVBI}	according to UL 60950-1 (edition 2). (certification pending)	1047	$\rm V_{RMS}$ or $\rm V_{DC}$		
		Maximum approved working voltage for reinforced isolation	730	V _{PK}		
Working Voltage for Reinforced Isolation	V _{WVRI}	according to UL 60950-1 (edition 2). (certification pending)	517	V_{RMS} or V_{DC}		
Clearance	D _{cl}	Minimum distance through air from IP leads to signal leads.	7.5	mm		
Creepage	D _{cr}	Minimum distance along package body from IP leads to signal leads	7.5	mm		

THERMAL CHARACTERISTICS

See https://www.allegromicro.com/en/Design-Center/Technical-Documents/Hall-Effect-Sensor-IC-Publications/DC-and-Transient-Current-Capability-Fuse-Characteristics.aspx.



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

FUNCTIONAL BLOCK DIAGRAM

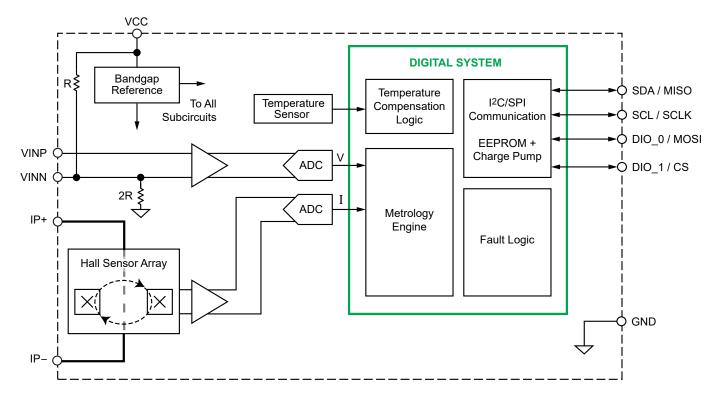


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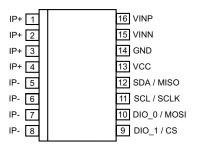
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Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection





Pinout Diagram

Terminal L	ist Table			
Number	Name	Desc	ription	
Number	Name	I2C	SPI	
1, 2, 3, 4	IP+	Terminals for current beir	ng sensed; fused internally	
5, 6, 7, 8	IP-	Terminals for current beir	ng sensed; fused internally	
9	DIO_1/CS	Digital I/O 1	Chip Select (CS)	
10	DIO_0/MOSI	Digital I/O 0	MOSI	
11	SCL/SCLK	SCL	SCLK	
12	SDA / MISO	SDA	MISO	
13	VCC	Device power	supply terminal	
14	GND	Device Power and S	ignal ground terminal	
15	VINN	Negative Input Voltage		
16	VINP	Positive In	put Voltage	

DIGITAL I/O

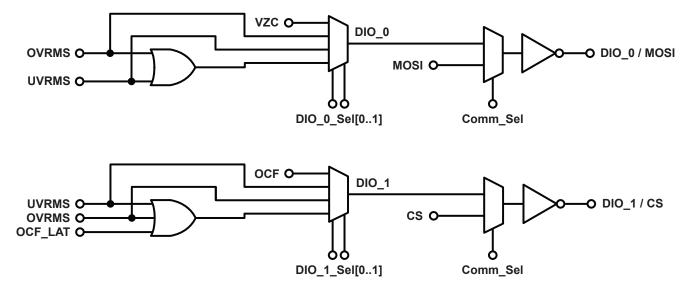
The Digital I/O can be programmed to represent the following functions (Digital Output pins are low true):

DIO_0:

- 0. VZC: Voltage zero crossing
- 1. OVRMS: The VRMS overvoltage flag
- 2. UVRMS: The VRMS undervoltage flag
- 3. The OR of OVRMS and UVRMS (if either flag is triggered, the DIO_0 pin will be asserted)

DIO_1:

- 0. OCF: Overcurrent fault
- 1. UVRMS: The VRMS undervoltage flag
- 2. OVRMS: The VRMS overvoltage flag
- The OR of OVRMS, UVRMS, and OCF_LAT [Latched Overcurrent fault] (if any of the three flags are triggered, the DIO_1 pin will be asserted)





Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
ELECTRICAL CHARACTERISTICS		l				
Supply Voltage	V _{CC}		V _{CC(nom)} × 0.9	V _{CC(nom)}	V _{CC(nom)} × 1.1	V
Supply Current	I _{CC}	$V_{CC}(min) \le V_{CC} \le V_{CC}(max)$, no load on output pins	-	12	14	mA
VOLTAGE BUFFER		·				
Differential Input Range	ΔV _{IN}	V _{INP} – V _{INN}	-275	_	275	mV
Common Mode Input Voltage	V _{IN(CM)}		$^{2/_{3}} \times V_{CC}$ - 0.275	_	^{2/} ₃ × V _{CC} + 0.275	V
VOLTAGE ADC			·			
Sample Frequency	f _S		-	32	-	kHz
Number of Bits	N _{ADC(V)}		_	16	_	bits
Voltage ADC Power Supply Rejection	V_PSRR	Ratio of change on V _{CC} to change in ADC internal reference at DC	60	70	-	dB
VOLTAGE SIGNAL CHAIN		•	· · · · · ·			
Noise	V _N		_	10	_	LSB
Internal Bandwidth	BW		_	1	-	kHz
Linearity Error	E _{LIN}		-	±0.2	-	%
CURRENT CHANNEL ADC						
Sample Frequency	f _S		-	32	-	kHz
Number of Bits	N _{ADC(I)}		-	16	-	bits
Current Channel ADC Power Supply Rejection	I_PSRR	Ratio of change on V _{CC} to change in ADC internal reference at DC	60	70	-	dB
CURRENT CHANNEL					· · · · · · · · · · · · · · · · · · ·	
Internal Bandwidth	BW		-	1	-	kHz
Primary Conductor Resistance	R _{IP}	T _A = 25°C	-	0.85	-	mΩ
Noise	V _N		-	100	-	LSB
Linearity Error	E _{LIN}		-	±1.5	-	%
OVERCURRENT FAULT CHARACTERISTICS	5					
Fault Response Time	t _{RF}	$ \begin{array}{l} \mbox{Time from } I_{P} \mbox{ rising above } I_{FAULT} \mbox{ until } \\ V_{FAULT} < V_{FAULT(max)} \mbox{ for a current} \\ \mbox{ step from 0 to } 1.2 \times I_{FAULT} \mbox{ 10 } \Omega \mbox{ and} \\ 100 \mbox{ pF from DIO}_1 \mbox{ to ground} \mbox{;} \\ \mbox{ fitdly set to 0} \end{array} $	_	5	_	μs
Internal Bandwidth	BW		_	200	_	kHz
Fault Hysteresis ^[2]	I _{HYST}		_	$0.05 \times I_{PR}$	_	А
Fault Range	I _{FAULT}	Set using FAULT field in EEPROM	0.5 × I _{PR}	_	1.75 × I _{PR}	А
VOLTAGE ZERO CROSSING						
	t _d			700		μs

^[1] Device may be operated at higher primary current levels, I_P, ambient, T_A, and internal leadframe temperatures, T_A, provided that the Maximum Junction Temperature, T_J(max), is not exceeded.

^[2] After I_P goes above I_{FAULT} , tripping the internal fault comparator, I_P must go below $I_{FAULT} - I_{HYST}$, before the internal fault comparator will reset.

Continued on next page ...



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

xKMATR-I2C OPERATING CHARACTERISTICS: Valid through the full range of T_A , $V_{CC} = V_{CC}(nom)$, $R_{EXT} = 10 \text{ k}\Omega$,

unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
I ² C INTERFACE CHARACTERISTICS ^[1]						
Bus Free Time Between Stop and Start	t _{BUF}		1.3	_	_	μs
Hold Time Start Condition	t _{hdSTA}		0.6	-	-	μs
Setup Time for Repeated Start Condition	t _{suSTA}		0.6	-	-	μs
SCL Low Time	t _{LOW}		1.3	-	-	μs
SCL High Time	t _{HIGH}		0.6	-	-	μs
Data Setup Time	t _{suDAT}		100	-	-	μs
Data Hold Time	t _{hdDAT}		0	-	900	μs
Setup Time for Stop Condition	t _{suSTO}		0.6	-	-	μs
Logic Input Low Level (SDA, SCL pins)	V _{IL}		-	-	30	%V _{CC}
Logic Input High Level (SDA, SCL pins)	V _{IH}		70	-	-	%V _{CC}
Logic Input Current	I _{IN}	Input voltage on SDA or SCL = 0 V to V_{CC}	-1	-	1	μA
Output Low Voltage (SDA)	V _{OL}	SDA sinking = 1.5 mA	-	-	0.36	V
Clock Frequency (SCL pin)	f _{CLK}		_	-	400	kHz
Output Fall Time (SDA pin)	t _f	$R_{EXT} = 2.4 \text{ k}\Omega, C_B = 100 \text{ pF}$	-	-	250	ns
I ² C Pull-Up Resistance	R _{EXT}		2.4	10	-	kΩ
Total Capacitive Load for Each of SDA and SCL Buses	C _B		_	_	20	pF

^[1] These values are ratiometric to the supply voltage, I²C Interface Characteristics are ensured by design and not factory tested.

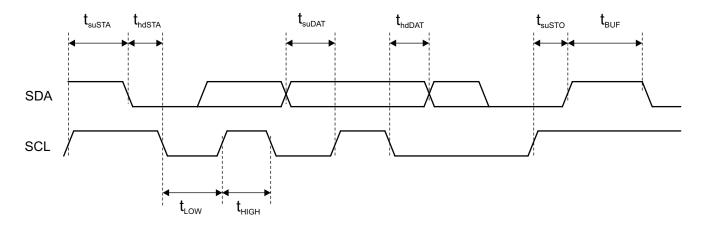


Figure 2: I²C Interface Timing



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

MATR-SPI OPERATING CHARACTERISTICS: Valid through the full range of T_A , $V_{CC} = V_{CC}$ (nom), unless otherwise specified
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Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
SPI INTERFACE CHARACTERISTIC	S					
		MOSI, SCLK, CS pins, V _{CC} (nom) = 3.3 V	2.8	-	3.63	V
Digital Input High Voltage	V _{IH}	MOSI, SCLK, CS pins, V _{CC} (nom) = 5 V	4	-	5.5	V
Digital Input Low Voltage	V _{IL}	MOSI, SCLK, CS pins	_	-	0.5	V
SDI Outout High Voltage	N	MISO pin, C_L = 20 pF, T_A = 25°C, V _{CC} (nom) = 3.3 V	2.8	3.3	3.8	V
SPI Output High Voltage	V _{OH}	MISO pin, C_L = 20 pF, T_A = 25°C, V _{CC} (nom) = 5 V	4	5	5.5	V
SPI Output Low Voltage	V _{OL}	MISO pin, C_L = 20 pF, T_A = 25°C	_	0.3	0.5	V
SPI Clock Frequency	f _{SCLK}	MISO pin, C _L = 20 pF	0.1	-	10	MHz
SPI Frame Rate	t _{SPI}		5.8	-	588	kHz
Chip Select to First SCLK Edge	t _{CS}	Time from CS going low to SCLK falling edge	50	_	-	ns
Data Output Valid Time	t _{DAV}	Data output valid after SCLK falling edge	_	40	-	ns
MOSI Setup Time	t _{SU}	Input setup time before SCLK rising edge	25	-	-	ns
MOSI Hold Time	t _{HD}	Input hold time after SCLK rising edge	50	-	_	ns
SCLK to CS Hold Time	t _{CHD}	Hold SCLK high time before CS rising edge	5	_	-	ns
Load Capacitance	CL	Loading on digital output (MISO) pin	_	-	20	pF

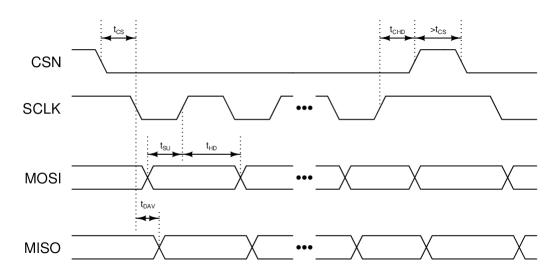


Figure 3: SPI Timing



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

ACS71020KMA-015B5 PERFORMANCE CHARACTERISTICS: Valid through the full operating temperature range, $T_A = -40^{\circ}$ C to 125°C, $C_{BYPASS} = 0.1 \mu$ F, and $V_{CC} = 5 V$, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. [1]	Max.	Unit
GENERAL CHARACTERISTICS						
Nominal Supply Voltage	V _{CC} (nom)		-	5	-	V
NOMINAL PERFORMANCE - CUI	RRENT CHANN	EL				
Current Sensing Range	I _{PR}		-15	_	15	А
Sensitivity	Sens _(I)	I_{PR} (min) < I_P < I_{PR} (max)	_	2184	-	LSB/A
ACCURACY PERFORMANCE - C	URRENT CHAN	INEL				
	_	Measured at $I_P = I_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±2	_	%
Total Output Error	E _{TOT(I)}	Measured at $I_P = I_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±3	_	%
TOTAL OUTPUT ERROR COMPO	NENTS – CURR	ENT CHANNEL				
Sensitivity Error		Measured at $I_P = I_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±1	_	%
	E _{SENS(I)}	Measured at $I_P = I_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±1.5	_	%
Offset Error	E _{O(I)}	$I_{P} = 0 \text{ A}, T_{A} = 25^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	_	±300	_	LSB
		$I_{P} = 0 \text{ A}, T_{A} = -40^{\circ}\text{C} \text{ to } 25^{\circ}\text{C}$	_	±500	-	LSB
NOMINAL PERFORMANCE - VOI	TAGE CHANNE	EL				
Sensitivity	Sens _(V)	V_{PR} (min) < V_{P} < V_{PR} (max)	_	238	_	LSB/mV
ACCURACY PERFORMANCE - V	OLTAGE CHAN	NEL				
		Measured at $V_P = V_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±1.2	_	%
Total Output Error	E _{TOT(V)}	Measured at $V_P = V_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±1.3	_	%
TOTAL OUTPUT ERROR COMPO	NENTS - VOLT	AGE CHANNEL				- 0
		Measured at $V_P = V_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±1	-	%
Sensitivity Error	E _{SENS(V)}	Measured at $V_P = V_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±1	_	%
		$V_{P} = 0 \text{ mV}, T_{A} = 25^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	_	±100	_	LSB
Offset Error	E _{O(V)}	$V_{P} = 0 \text{ mV}, T_{A} = -40^{\circ}\text{C to } 25^{\circ}\text{C}$	_	±150	_	LSB
ACCURACY PERFORMANCE - A	CTIVE POWER					
Total Output Error		Measured at $V_P = V_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±2.3	_	%
Total Output Error	E _{TOT(P)}	Measured at $V_P = V_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±3.3	-	%

^[1] Typical values are based on mean ±3 sigma.



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

ACS71020KMA-030B3 PERFORMANCE CHARACTERISTICS: Valid through the full operating temperature range, $T_A = -40^{\circ}$ C to 125°C, $C_{BYPASS} = 0.1 \mu$ F, and $V_{CC} = 3.3$ V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. [1]	Max.	Unit
GENERAL CHARACTERISTICS		· · · · · · · · · · · · · · · · · · ·		·		
Nominal Supply Voltage	V _{CC} (nom)		_	3.3	_	V
NOMINAL PERFORMANCE - C	URRENT CHANN	EL		·		
Current Sensing Range	I _{PR}		-30	_	30	A
Sensitivity	Sens _(I)	I_{PR} (min) < I_{P} < I_{PR} (max)	_	1092	_	LSB/A
ACCURACY PERFORMANCE -	CURRENT CHAN	INEL				
		Measured at $I_P = I_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±2	_	%
Total Output Error	E _{TOT(I)}	Measured at $I_P = I_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±3	-	%
TOTAL OUTPUT ERROR COMP	ONENTS - CURR	RENT CHANNEL			,	
Sensitivity Error	_	Measured at $I_P = I_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±1	_	%
	E _{SENS(I)}	Measured at $I_P = I_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±1.5	-	%
0.5		$I_{P} = 0 \text{ A}, T_{A} = 25^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	_	±500	-	LSB
Offset Error	E _{O(I)}	$I_{P} = 0 \text{ A}, T_{A} = -40^{\circ}\text{C} \text{ to } 25^{\circ}\text{C}$	_	±700	_	LSB
NOMINAL PERFORMANCE - VO	OLTAGE CHANNE	EL		·		
Sensitivity	Sens _(V)	V_{PR} (min) < V_{P} < V_{PR} (max)	_	238	_	LSB/mV
ACCURACY PERFORMANCE -	VOLTAGE CHAN	NEL				
	_	Measured at $V_P = V_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±1.2	_	%
Total Output Error	E _{TOT(V)}	Measured at $V_P = V_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±1.3	-	%
TOTAL OUTPUT ERROR COMP	ONENTS - VOLT	AGE CHANNEL				
o	_	Measured at $V_P = V_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±1	_	%
Sensitivity Error	E _{SENS(V)}	Measured at $V_P = V_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±1	_	%
		$V_{\rm P} = 0 \text{ mV}, T_{\rm A} = 25^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	_	±60	_	LSB
Offset Error	E _{O(V)}	$V_{\rm P} = 0 \text{ mV}, T_{\rm A} = -40^{\circ}\text{C to } 25^{\circ}\text{C}$	_	±80	_	LSB
ACCURACY PERFORMANCE -	ACTIVE POWER	· · ·				
	_	Measured at $V_P = V_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±2.3	_	%
Total Output Error	E _{TOT(P)}	Measured at $V_P = V_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±3.3	_	%

^[1] Typical values are based on mean ±3 sigma.



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

ACS71020KMA-090B3 PERFORMANCE CHARACTERISTICS: Valid through the full operating temperature range, $T_A = -40^{\circ}$ C to 125°C, $C_{BYPASS} = 0.1 \mu$ F, and $V_{CC} = 3.3$ V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. [1]	Max.	Unit
GENERAL CHARACTERISTICS	, ,					
Nominal Supply Voltage	V _{CC} (nom)		_	3.3	-	V
NOMINAL PERFORMANCE - C	JRRENT CHANN	EL				
Current Sensing Range	I _{PR}		-90	-	90	Α
Sensitivity	Sens _(I)	I_{PR} (min) < I_{P} < I_{PR} (max)	_	364	_	LSB/A
ACCURACY PERFORMANCE -	CURRENT CHAN	INEL				
		Measured at $I_P = I_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±2	_	%
Total Output Error	E _{TOT(I)}	Measured at $I_P = I_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±3	-	%
TOTAL OUTPUT ERROR COMP	ONENTS - CURR	RENT CHANNEL				
		Measured at $I_P = I_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±1	_	%
Sensitivity Error	E _{SENS(I)}	Measured at $I_P = I_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±1.5	_	%
		$I_{P} = 0 \text{ A}, T_{A} = 25^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	_	±300	_	LSB
Offset Error	E _{O(I)}	$I_{P} = 0 \text{ A}, T_{A} = -40^{\circ}\text{C} \text{ to } 25^{\circ}\text{C}$	_	±500	_	LSB
NOMINAL PERFORMANCE - VO	DLTAGE CHANNE	ĒL				
Sensitivity	Sens _(V)	V_{PR} (min) < V_{P} < V_{PR} (max)	_	238	_	LSB/mV
ACCURACY PERFORMANCE -	VOLTAGE CHAN	NEL				-
T		Measured at $V_P = V_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±1.2	_	%
Total Output Error	E _{TOT(V)}	Measured at $V_P = V_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±1.3	-	%
TOTAL OUTPUT ERROR COMP	ONENTS - VOLT	AGE CHANNEL		·		
		Measured at $V_P = V_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±1	_	%
Sensitivity Error	E _{SENS(V)}	Measured at $V_P = V_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±1	_	%
0%		$V_{P} = 0 \text{ mV}, T_{A} = 25^{\circ}\text{C} \text{ to } 125^{\circ}\text{C}$	_	±100	_	LSB
Offset Error	E _{O(V)}	$V_{P} = 0 \text{ mV}, T_{A} = -40^{\circ}\text{C to } 25^{\circ}\text{C}$	_	±150	_	LSB
ACCURACY PERFORMANCE -	ACTIVE POWER	· · · · ·				
Tabal Quebeurt Erman		Measured at $V_P = V_{PR}$ (max), $T_A = 25^{\circ}C$ to $125^{\circ}C$	_	±2.3	_	%
Total Output Error	E _{TOT(P)}	Measured at $V_P = V_{PR}$ (max), $T_A = -40^{\circ}$ C to 25°C	_	±3.3	-	%

 $\ensuremath{^{[1]}}$ Typical values are based on mean ±3 sigma.



DATA ACQUISITION

ADCs

Both the Current and Voltage channels are sampled at a high frequency and then digitally filtered and decimated to avoid large anti-aliasing filters. The final sample rate will be near 32 kHz for an 8 MHz clock. The digital low-pass filters are EEPROM programmable and have a cutoff from 1 to 8 kHz. The digital word from the ADC is 16 bits for both the current and the voltage.

Raw Signal Sensitivity and Offset Trim

The gain and offset for both current and voltage channels use a shared temperature compensation engine which is trimmed in production. The fine sensitivity and offset are also trimmed in production at the factory; however, the user has access to the fine sensitivity field for the current channel should they want to trim the gain in application.

Phase Compensation

Phase delay may be introduced on either the voltage or current channels. The range is EEPROM selectable, either 5° of delay (step size of 0.67°) or 40° of delay (step size of 5.36°).

Zero Crossing

The zero crossings are only detected on the voltage signal. Both the high-to-low and low-to-high transitions will be detected with time-based hysteresis that removes the possibility of noise causing multiple zero crossings to be reported at each true zero crossing.

The zero crossing output can be a square wave that transitions at each zero crossing or a pulse with a fixed width at each zero crossing. When in pulse mode, the width of the pulse is t_p (see delaycnt_sel; nominal setting is 32 μ s). There will be a fixed delay, t_D , from the time that a true zero crossing has occurred to the time that it is reported. This delay helps to keep the zero crossing detection more precise.

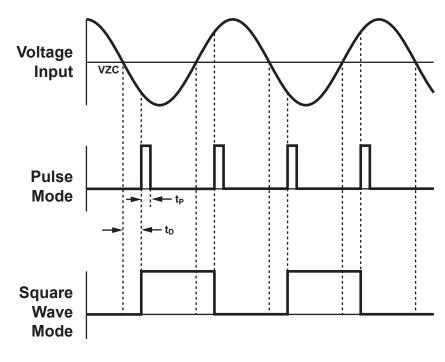


Figure 4: Zero Crossing



POWER CALCULATIONS

I_{RMS} / V_{RMS}

Cycle by cycle calculation of the root mean square of both the current and voltage channels:

$$I_{RMS} = \sqrt{\frac{\sum_{n=0}^{n=N-1} I_n^2}{N}} \qquad V_{RMS} = \sqrt{\frac{\sum_{n=0}^{n=N-1} V_n^2}{N}}$$

where In (Icodes) and Vn (Vcodes) are the instantaneous measurements of current and voltage, respectively.

Active Power

The real component of power being measured; calculated cycle by cycle:

$$P_{ACTIVE} = \frac{\sum_{n=0}^{n=N-1} P_n}{N} \qquad P_n = I_n \times V_n$$

Apparent Power

The magnitude of the complex power being measured; calculated at the end of each cycle:

$$|S| = I_{RMS} \times V_{RMS}$$

Reactive Power

Imaginary component of power being measured; calculated at the end of each cycle:

$$Q = \sqrt{S^2 - P_{ACTIVE}^2}$$

Power Factor

The magnitude of the ratio of real power to apparent power; calculated at the end of each cycle:

$$|PF| = \frac{P_{ACTIVE}}{|S|}$$

Lead/Lag

The voltage leading or lagging the current will be communicated as a single bit. This bit also represents the sign of the Apparent Power.



Overcurrent Fault

The overcurrent fault threshold may be set from 50% to 175% of I_P. The user sets the trip point with an 8-bit word. The user also has the ability to set the trip level digital delay. This allows for up to a 32 μ s delay on the Fault.

Averaging Over Time

The following values can be averaged over a programmable number of updates:

- IRMS or VRMS
- PACTIVE

The number of averages is controlled by two different registers. There is an accumulator that averages the above values. A 7-bit number, rms_avg_1, is used to determine the number of averages. There is an additional accumulator that will be used to average the output of the first accumulator. There is a 10-bit number, rms_avg_2, that will be used to determine the number of averages for this accumulator. The combination of the two accumulator allows the user to select how long to average for as well as how often the values are updated. The exact time this averages over depends on n (the number of samples per cycle). Averages could be read in Reg 0x26 to 0x29.

Over/Undervoltage Detection

There are two flags that can be used to detect undervoltage and overvoltage. These flags have a programmable voltage trip level. Refer to the Digital I/O section for all possible configurations.

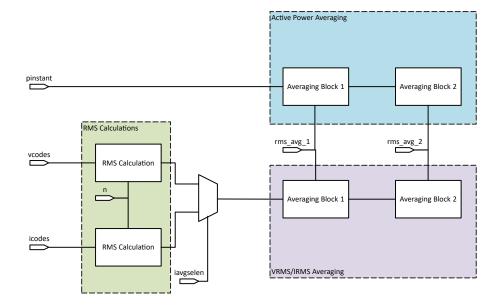


Figure 5: ACS71020 Trim Diagram



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

DIGITAL COMMUNICATION

Communication Interfaces

The ACS71020 supports communication over 1 MHz $I^{2}C$ and 10 MHz SPI. However, the communication protocol is fixed during factory programming. Refer to the Selection Guide for more information.

SPI

The SPI frame consists of:

- The Master writes on the MOSI line the 7-bit address of the register to be read from or written to.
- The next bit on the MOSI line is the RW indicator. A high state indicates a Read and a low state indicates a Write.
- On the next 32 bits, the MISO line contains the response to the previous command.
- On the MOSI line, if the current command is a write, the 32 bits correspond to the Write data, and in case of a write the data is ignored.

Registers and EEPROM

WRITE ACCESS

The ACS71020 supports factory and customer EEPROM space as well as volatile registers. The customer access code must be sent prior to writing these customer EEPROM spaces. In addition, the device includes a set of free space EEPROM registers that are accessible with or without writing the access code.

READ ACCESS

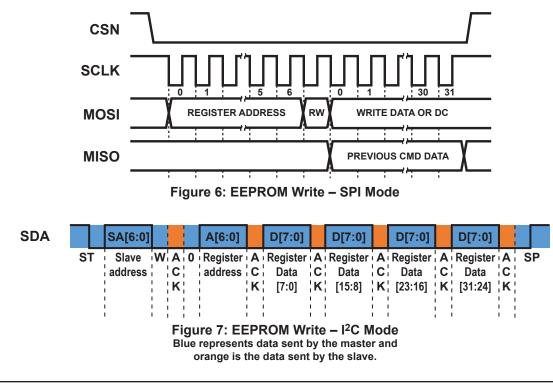
All EEPROM and volatile registers may be read at any time regardless of the access code.

EEPROM

All configuration EEPROM will be shadowed to volatile memory, and the shadow registers are loaded from EEPROM on power-up. The shadow registers can be written to in order to change the device behavior without having to perform an EEPROM write. Any changes made it shadow memory are volatile and do not persist through a reset event.

WRITING

The Timing Diagram for an EEPROM write is shown in Figure 6 and Figure 7.

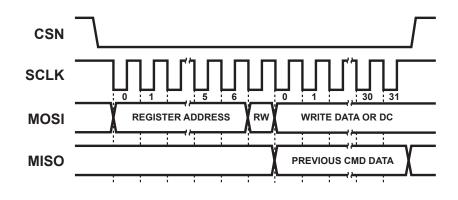


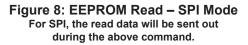


Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

READING

The timing diagram for an EEPROM read is shown in Figure 8 and Figure 9.





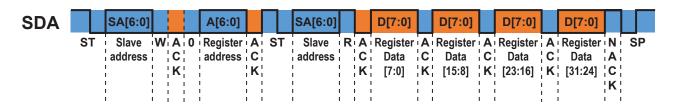


Figure 9: EEPROM Read – I²C Mode Blue represents data sent by the master and orange is the data sent by the slave.



ACS71020 Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

EEPROM Error Checking and Correction (ECC)

Hamming code methodology is implemented for EEPROM checking and correction (ECC). ECC is enabled after power-up.

The ACS71020 analyzes message data sent by the controller and the ECC bits are added. The first 6 bits sent from the device to the controller are dedicated to ECC. The device always returns 32 bits.

EEPROM ECC Errors

Name	Description
_	No meaning
ECC	00 = No Error 01 = Error detected and message corrected 10 = Uncorrectable error 11 = No meaning
D[25:0]	EEPROM data
	- ECC



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

MEMORY MAP

EEPROM/Shadow Memory

	Address												Bits											
	Ă	31 30 29	28	27 26	25	24	23	22	21	20	19 18	17 1	16 15 14	13 12	11	10 9	8	7	6	5	4	3	2	1 0
	0x0B	ECC							iavgselen	cr	s_sns		s	ns_fine		<u> </u>				qv	vo_fin	e		
	0x0C	EC	CC						n					rms_	_avg_	2			rms_avg_1					
EEPROM	0x0D	ECC			squarewave_en	halfcycle_en	1	fitdly				faul	t			chan_del_sel		ichan_del_en			pac	c_trir	n	
EE	0x0E	EC	сс							delaycnt_sel	ι	underv	vreg		over	vreg		bypass_n_en	vadc_rate_set		ve	vent_	cycs	
	0x0F	ECC									dio_1_sel	dio_0_sel				i2c_dis_slv_addr			i2c_	slv_a	addr			
	0x1B								iavgselen	crs_sns sns_fine								qv	∕o_fin	e				
	0x1C								n					rms_avg_2						rms_avg_1				
Shadow	0x1D				squarewave_en	halfcycle_en	1	fltdly				fa	ault		unused	chan_del_sel		unused	ichan_del_en		р	acc_t	rim	
Sha	0x1E									delaycnt_sel		unde	ervreg			overvreg			bypass_n_en	vadc_rate_set	,	vever	it_cy	cs
	0x1F									dio_1_sel			i2c_dis_slv_addr			i2c_	slv_a	addr						



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Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

Device Trim Flow

The trim process for voltage, current, and power channels are depicted in Figure 10 through Figure 12. Refer to the "Register Details" Section for more information regarding trim fields.

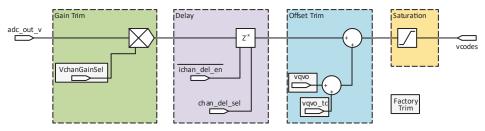


Figure 10: Voltage Channel Trim Flow

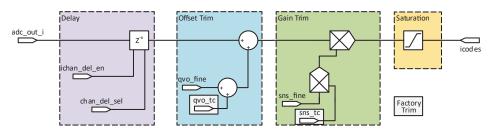


Figure 11: Current Channel Trim Flow

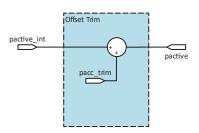


Figure 12: Power Channel Trim Flow



Register Details – EEPROM

Register 0x0B/0x1B

Bits	Name	Description
8:0	qvo_fine	Offset fine trimming on current channel
17:9	sns_fine	Fine gain trimming on the current channel
20:18	crs_sns	Coarse gain setting
21	iavgselen	Current Averaging selection
25:22	unused	Unused
31:26	ecc	Error Code Correction

qvo_fine

Offset adjustment for the current channel. This is a signed 9-bit number and ranges from -256 to 255. With a step size of 64 LSB this equates to an offset trim range of -16384 to 16320 LSB added to the icodes value. The trim is implemented as shown in Figure 11. The offset trim on the current channel should be done before the gain trim. Settings are further described in Table 1.

Table 1: qvo_fine

Range	Value	Units
-256 to 255	-16,384 to 16,320	LSB

sns_fine

Gain adjustment for the current channel. This is a signed 9-bit number so it can range from -256 to 255. This gain adjustment is implemented as a percentage multiplier centered around 1 (i.e. writing a 0 to this field multiplies the gain by 1, leaving the gain unaffected). The range then equates to 0.5 to 1.5 (nominal sensitivity $\pm 50\%$). The offset trim on the current channel should be done before the gain trim. Settings are further described in Table 2.

Table 2: sns_fine

Range	Value	Units
-256 to 255	0.5 to 1.5	_

crs_sns

Table 3: crs sns

Coarse gain adjustment for the current channel. This gain is implemented in the analog domain before the ADC. This is a 3-bit number that allows for 8 gain selections. Changing these settings will likely change the device performance over temperature so the temperature accuracy is only guaranteed in the crs_sns setting that was set in factory. The gain settings map to $1\times$, $2\times$, $3\times$, $3.5\times$, $4\times$, $4.5\times$, $5.5\times$, and $8\times$. Settings are further described in Table 3.

Range	Value	Units			
0	1×	-			
1	2×	-			
2	3×	-			
3	3.5×	-			
4	4×	-			
5	4.5×	-			
6	5.5×	-			
7	8×	-			

iavgselen

Current Averaging selection. 0 will select vrms for averaging. 1 will select irms for averaging. See Figure 5.



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

Register 0x0C/0x1C

Bits	Name	Description
6:0	rms_avg_1	Average of the rms voltage or current – stage 1
16:7	rms_avg_2	Average of the rms voltage or current – stage 2
25:17	n	Number of samples per half period.
31:26	ecc	Error Code Correction

rms_avg_1

Number of averages for the first averaging stage (vrmsavgonesec or irmsavgonesec). The value written into this field directly maps to the number of averages ranging from 0 to 127. The channel to be averaged is selected by iavgselen.

Table 4: rms_avg_1

Range	Value	Units
0 to 127	0 to 127	number of averages

rms_avg_2

Number of averages for the second averaging stage (vrmsavgonemin or irmsavgonemin). This stage averages the outputs of the first averaging stage. The value written into this field directly maps to the number of averages ranging from 0 to 1023. The channel to be averaged is selected by iavgselen.

Table 5: rms_avg_2

Range	Value	Units			
0 to 1023	0 to 1023	number of averages			

n

This is the number of samples to be used in all rms calculations if the bypass_n_en is set. If $bypass_n_en$ is 0 (Reg 0x0E), then this field is unused. The value written into this field directly maps to the number of samples ranging from 0 to 511.

Table 6: n

Range	Value	Units
0 to 511	0 to 511	number of samples



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

Register 0x0D/0x1D

Bits	Name	Description
6:0	pacc_trim	Trims the active power
7	ichan_del_en	Selects which channel gets delayed
8	unused	unused
11:9	chan_del_sel	Selects the amount of delay for the channel being delayed
12	unused	unused
20:13	fault	Fault level setting
23:21	fltdly	Fault delay count bits
24	halfcycle_en	Outputs pulses at every zero crossing when enabled, and every rising edge when disabled
25	squarewave_en	Selects pulse or square wave output for the zero crossing reporting
31:26	ecc	Error Code Correction

pacc_trim

Offset trim in the active power calculation. Implemented as shown in Figure 12. This is a 7-bit signed number. This then equates to a trim of -384 to 378 LSB to be added to the pactive value.

Table 7: pacc_trim

<u> </u>		
Range	Value	Units
-64 to 63	-384 to 378	LSB

ichan_del_en

Enables delay for either the voltage or current channel. Setting to 1 enables delay for the current channel. This behavior is depicted in Figure 10 and Figure 11.

Table 8: ichan_del_en

Range	Value	Units
0	0 – voltage channel	LSB
1	1 – current channel	LSB

chan_del_sel

Selection of delays applied to the channel based on ichan_del_en section. The step size of this field is determined by the value of vadc_rate_sel.

Table 9: chan_del_sel

vadc_rate_sel	Range	Value[x]	Units
0	0 to 7	0 to 219	μs
1	0 to 7	0 to 875	μs

fault

Overcurrent fault threshold. This field is an 8-bit number ranging from 0 to 255. This equates to a fault range of 0.5 to 1.75 %I_P. The factory setting of this field is 0.

Table 10: fault

Range	Value	Units
0 to 255	0.5 to 1.75	%I _P

fltdly

Fault delay setting of the amount of delay applied before flagging a fault condition.

Table 11: fltdly

Range	Value	Units
0	0	μs
1	0	μs
2	4.75	μs
3	9.25	μs
4	13.75	μs
5	18.5	μs
6	23.25	μs
7	27.75	μs

halfcycle_en

Setting for the voltage zero-crossing detection. When set to 0, the voltage zero-crossing will be indicated on every rising edge. When set to 1, the voltage zero-crossing will be indicated on both rising and falling edges.



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

squarewave_en

Setting for the voltage zero-crossing detection. When set to 0, if the voltage zero-crossing is being output on a DIO pin, then the event will be indicated by a pulse on the DIO pin. When set to 1, if the voltage zero-crossing is being output on a DIO pin, then the event will be indicated by a level change on the DIO pin.



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

Register 0x0E/0x1E

Bits	Name	Description
5:0	vevent_cycs	Sets the number of qualifying cycles needed to flag overvoltage or undervoltage
6	vadc_rate_set	Sample Frequency Selection
7	bypass_n_en	When enabled, the dynamic calibration of n is ignored and instead uses the programmed n value for computations
13:8	overvreg	Level to flag overvoltage
19:14	undervreg	Level to flag undervoltage
20	delaycnt_sel	Selects zero cross output pulse width
25:21	unused	Unused
31:26	ecc	Error Code Correction

vevent_cycs

Setting to determine the number of cycles required to set the OVRMS flag or the UVRMS flag. This is a 6-bit number ranging from 0 to 63. The value in this field directly maps to the number of cycles.

Table 12: vevent_cycs

Range	Value	Units
0 to 63	1 to 64	cycles

vadc_rate_set

Rate selection for the ADC update. Setting this field to a 0 selects a 32 kHz update. Setting this field to a 1 selects an 8 kHz update. The setting of this field to 1 will reduce the number of samples used in each rms calculation, but it will allow for a larger phase delay correction between channels (see chan_del_sel).

Table 13: vadc_rate_set

Range	Value	Units
0	32	kHz
1	8	kHz

bypass_n_en

When enabled, the dynamic calibration of n is ignored and instead uses the programmed n value for computations.

overvreg

Setting for the trip level of the overvoltage rms flag (ovrms). This is a 6-bit number ranging from 0 to 63. This trip level spans the entire range of the vrms register. The flag is set if the rms value is above this threshold for the number of cycles selected in vevent_cycs.

Table 14: overvreg

Range	Value	Units
0 to 63	0 to 32,768	LSB

undervreg

Setting for the trip level of the undervoltage rms flag (uvrms). This is a 6-bit number ranging from 0 to 63. This trip level spans one entire range of the vrms register. The flag is set if the rms value is below this threshold for the number of cycles selected in vevent_cycs.

Table 15: undervreg

Range	Value	Units
0 to 63	0 to 32,768	LSB

delaycnt_sel

Selection bit for the width of pulse for a voltage zero-crossing event. When set to 0, the pulse is $32 \ \mu$ s. When set to 1, the pulse is $256 \ \mu$ s. When the squarewave_en bit is set, this field is ignored.

Table 16: delaycnt_sel

Range	Value	Units
0	32	μs
1	256	μs



Single Phase, Isolated, Power Monitoring IC with Voltage Zero Crossing and Overcurrent Detection

Register 0x0F/0x1F

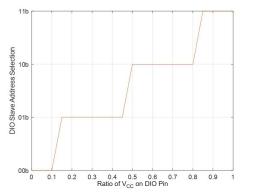
Bits	Name	Description
1:0	unused	Unused
8:2	i2c_slv_addr	I ² C slave address selection
9	i2c_dis_slv_addr	Disable I ² C slave address selection circuit
15:10	unused	Unused
17:16	dio_0_sel	Digital output 0 multiplexor selection bits
19:18	dio_1_sel	Digital output 1 multiplexor selection bits
25:20	unused	Unused
31:26	ecc	Error Code Correction

i2c_slv_addr

Settings for the I²C slave address. The voltage on the DIO pins will be measured at power up and this will be used to select the slave address that the device will respond to. This can be kept down with a resistor divider off of $V_{\rm CC}$. Each DIO pin has 4 different regions that affect the slave address chosen as shown in the figure below.

Table 17: i2c_slv_addr

DIO_1		DIO_0		A6	A5	A4	A3	A2	A1	A0	Slave Address (decimal)
0	0	0	0	1	1	0	0	0	0	0	96
0	0	0	1	1	1	0	0	0	0	1	97
0	0	1	0	1	1	0	0	0	1	0	98
0	0	1	1	1	1	0	0	0	1	1	99
0	1	0	0	1	1	0	0	1	0	0	100
0	1	0	1	1	1	0	0	1	0	1	101
0	1	1	0	1	1	0	0	1	1	0	102
0	1	1	1	1	1	0	0	1	1	1	103
1	0	0	0	1	1	0	1	0	0	0	104
1	0	0	1	1	1	0	1	0	0	1	105
1	0	1	0	1	1	0	1	0	1	0	106
1	0	1	1	1	1	0	1	0	1	1	107
1	1	0	0	1	1	0	1	1	0	0	108
1	1	0	1	1	1	0	1	1	0	1	109
1	1	1	0	1	1	0	1	1	1	0	110
1	1	1	1	EE	EEPROM value						



i2c_dis_slv_addr

This bit is used to disable the analog portion of the I²C slave address that is done on power on. When this bit is set, the i2c_slv_addr will directly set the slave address.

dio_0_sel

Selection bits for which flags are output on the DIO0 pin. Only used when the device is in $I^{2}C$ programming mode.

Table	18:	dio	0	sel

Value	Selection			
0	VZC: Voltage zero crossing			
1	OVRMS: The VRMS overvoltage flag			
2	UVRMS: The VRMS undervoltage flag			
3	The OR of OVRMS and UVRMS (if either flag is triggered, the DIO_0 pin will be asserted)			

dio_1_sel

Selection bits for which flags are output on the DIO1 pin. Only used when the device is in $I^{2}C$ programming mode.

Table 19: dio_1_sel

Value	Selection				
0	OCF: Overcurrent fault				
1	UVRMS: The VRMS undervoltage flag				
2	OVRMS: The VRMS overvoltage flag				
3	The OR of OVRMS, UVRMS, and OCF (if any of the three flags are triggered, the DIO_0 pin will be asserted).				

